

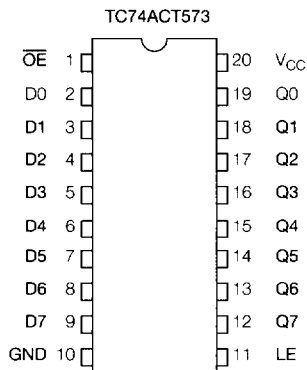
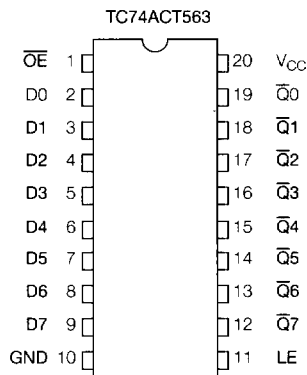
## TC74ACT563, 573 Octal D-Type Latch with 3-State Output

563: Inverting  
573: Non-Inverting

### Features:

- **High Speed:**  $t_{pd} = 5.5\text{ns}$  (typ.) at  $V_{CC} = 5\text{V}$
- **Low Power Dissipation:**  $I_{CC} = 8\mu\text{A}$  (max.) at  $T_a = 25^\circ\text{C}$
- **Compatible with TTL Outputs:**  $V_{IL} = 0.8\text{V}$  (max.);  $V_{IH} = 2.0\text{V}$  (min.)
- **Symmetrical Output Impedance:**  $I_{OH} = I_{OL} = 24\text{mA}$  (min.). Capability of driving  $50\Omega$  transmission lines.
- **Balanced Propagation Delays:**  $t_{pLH} = t_{pHL}$
- **Pin and Function Compatible with 74F563/573**
- **ACT563 Available in DIP, SOIC and SOP Packages**
- **ACT573 Available in DIP, SOIC, SOP and SSOP Packages**

### Pin Assignment



The TC74ACT563 and TC74ACT573 are advanced high speed CMOS OCTAL LATCHES with 3-STATE OUTPUTS fabricated with silicon gate and double-layer metal wiring C<sup>2</sup>MOS technology.

They achieve the high speed operation similar to equivalent Bipolar Schottky TTL, while maintaining the CMOS low power dissipation.

These devices may be used as a level converters for interfacing TTL or NMOS to high speed CMOS. The inputs are compatible with TTL, NMOS and CMOS output voltage levels.

These 8-bit D-type latches are controlled by a latch enable input (LE) and a output enable input ( $\overline{OE}$ ).

When the  $\overline{OE}$  input is high, the eight outputs are in a high impedance state.

The TC74ACT573 is an inverting type, and the TC74ACT563 is a non-inverting type.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

### Truth Table

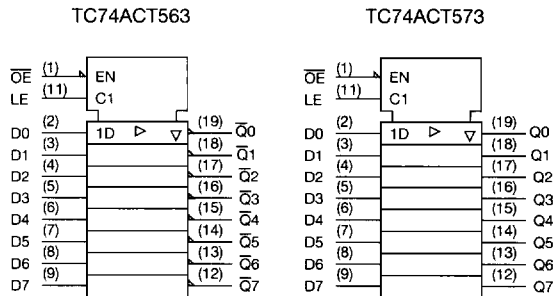
INPUTS			OUTPUTS	
$\overline{OE}$	LE	D	Q(573)	$\overline{Q}$ (563)
H	X	X	Z	Z
L	L	X	$Q_n$	$\overline{Q}_n$
L	H	L	L	H
L	H	H	H	L

X: Don't Care

Z: High Impedance

$Q_n$  ( $\overline{Q}_n$ ): Q ( $\overline{Q}$ ) outputs are latched at the time when the LE input is taken to a low logic level.

### IEC Logic Symbol



## Absolute Maximum Ratings

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	$V_{CC}$	-0.5-7.0	V
DC Input Voltage	$V_{IN}$	-0.5- $V_{CC} + 0.5$	V
DC Output Voltage	$V_{OUT}$	-0.5- $V_{CC} + 0.5$	V
Input Diode Current	$I_{IK}$	$\pm 20$	mA
Output Diode Current	$I_{OK}$	$\pm 50$	mA
DC Output Current	$I_{OUT}$	$\pm 50$	mA
DC $V_{CC}$ /Ground Current	$I_{CC}$	$\pm 200$	mA
Power Dissipation	$P_D$	500 (DIP) */180 (SOP)	mW
Storage Temperature	$T_{stg}$	-65-150	$^{\circ}C$
Lead Temperature 10sec	$T_L$	300	$^{\circ}C$

\* 500mW in the range of  $T_a = -40^{\circ}C$ - $65^{\circ}C$ .  
From  $T_a = 65^{\circ}C$  to  $85^{\circ}C$  a derating factor of  
-10mW/ $^{\circ}C$  should be applied up to 300mW.

## Recommended Operating Conditions

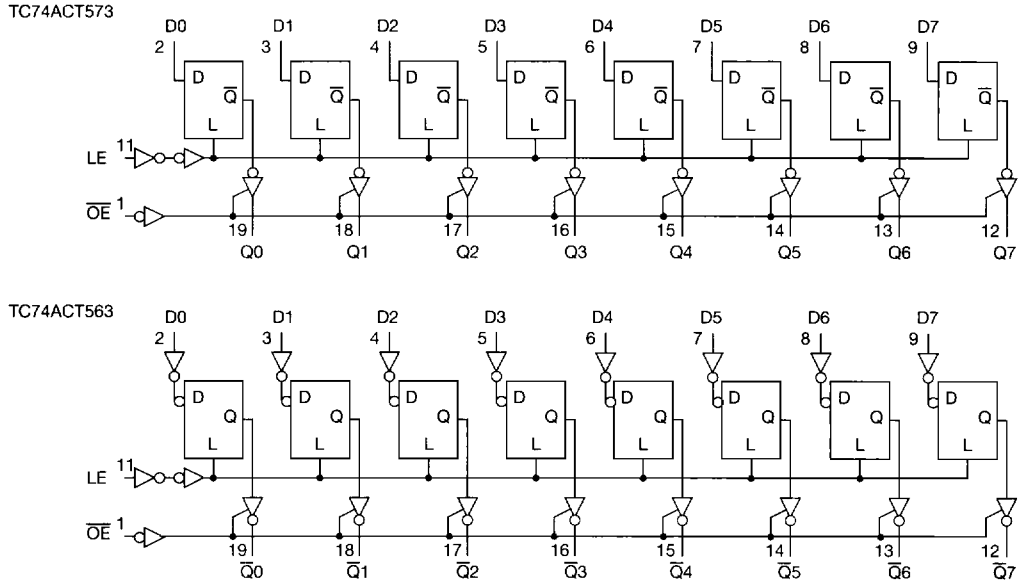
PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	$V_{CC}$	4.5-5.5	V
Input Voltage	$V_{IN}$	0- $V_{CC}$	V
Output Voltage	$V_{OUT}$	0- $V_{CC}$	V
Operating Temperature	$T_{opr}$	-40-85	$^{\circ}C$
Input Rise and Fall Time	$dt/dv$	0-10	ns/v

## DC Electrical Characteristics

PARAMETER	SYMBOL	TEST CONDITION	$T_a = 25^{\circ}C$			$T_a = -40$ - $85^{\circ}C$		UNIT		
			$V_{CC}$	Min.	Typ.	Max.	Min.		Max.	
High-Level Input Voltage	$V_{IH}$		4.5-5.5	2.0	—	—	2.0	—	V	
Low-Level Input Voltage	$V_{IL}$		4.5-5.5	—	—	0.8	—	0.8	V	
High-Level Output Voltage	$V_{OH}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OH} = -50\mu A$	4.5	4.4	4.5	—	4.4	—	V
			$I_{OH} = -24mA$	4.5	3.94	—	—	3.80	—	
			$I_{OH} = -75mA^*$	5.5	—	—	—	3.85	—	
Low-Level Output Voltage	$V_{OL}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OL} = 50\mu A$	4.5	—	0.0	0.1	—	0.1	V
			$I_{OL} = 24mA$	4.5	—	—	0.36	—	0.44	
			$I_{OL} = 75mA^*$	5.5	—	—	—	—	1.65	
3-State Output Off-State Current	$I_{OZ}$	$V_{IN} = V_{IH}$ or $V_{IL}$ $V_{OUT} = V_{CC}$ or GND	5.5	—	—	$\pm 0.5$	—	$\pm 5.0$	$\mu A$	
Input Leakage Current	$I_{IN}$	$V_{IN} = V_{CC}$ or GND	5.5	—	—	$\pm 0.1$	—	$\pm 1.0$		
Quiescent Supply Current	$I_{CC}$	$V_{IN} = V_{CC}$ or GND	5.5	—	—	8.0	—	80.0		
	$\Delta I_{CC}$	Per input: $V_{CC} = 3.4V$ Other input: $V_{CC}$ or GND	5.5	—	—	1.35	—	1.5	mA	

\* This spec indicates the capability of driving  $50\Omega$  transmission lines.  
One output should be tested at a time for a 10ms maximum duration.

System Diagram



Timing Requirements (Input  $t_r = t_f = 3n$ )

PARAMETER	SYMBOL	TEST CONDITION	Ta=25°C		Ta=-40-85°		UNIT
			V <sub>CC</sub>	Typ.	Max.	Max.	
Minimum Pulse Width (LE)	$t_{W(H)}$	—	5.0±0.5	—	5.0	5.0	ns
Minimum Set-up Time	$t_s$	—	5.0±0.5	—	3.0	3.0	
Minimum Hold Time	$t_h$	—	5.0±0.5	—	2.0	2.0	

AC Electrical Characteristics (C<sub>L</sub> = 50pF, R<sub>L</sub> = 500Ω, Input  $t_r = t_f = 3ns$ )

PARAMETER	SYMBOL	TEST CONDITION	Ta = 25°C			Ta = -40-85°C		UNIT	
			V <sub>CC</sub>	Min.	Typ.	Max.	Min.		Max.
Propagation Delay Time (LE-Q, Q̄)	$t_{pLH}$ $t_{pHL}$	—	5.0±0.5	—	6.3	10.5	1.0	12.0	ns
Propagation Delay Time (Dn-Q, Q̄)	$t_{pLH}$ $t_{pHL}$	—	5.0±0.5	—	6.2	9.6	1.0	11.0	
Output Enable Time	$t_{pZL}$ $t_{pZH}$	—	5.0±0.5	—	6.5	10.0	1.0	11.5	
Output Disable Time	$t_{pLZ}$ $t_{pHZ}$	—	5.0±0.5	—	6.5	8.8	1.0	10.0	
Input Capacitance	C <sub>IN</sub>	—	—	—	5	10	—	10	pF
Output Capacitance	C <sub>OUT</sub>	—	—	—	10	—	—	—	
Power Dissipation Capacitance	C <sub>PD</sub>	—	—	—	22	—	—	—	

Note (1): C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC (opr)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>IN</sub> + I<sub>CC</sub> / 8 (per Latch). And the total C<sub>PD</sub> when n pcs. of Latch operate can be gained by the following equation: C<sub>PD (total)</sub>=6+16 • n.